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CRAARTOS 449 (Modified) SERIAL NO. ATTY. DOCKET NO. FIS920040150US1 10/710,608 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT: APPLICANTS INFORMATION DISCLOSURE Kangguo CHENG, et al. **STATEMENT** GROUP: FILING DATE: (Use several sheets if necessary) Unassigned 07/23/2004 **U.S. PATENT DOCUMENTS** REFERENCE DESIGNATION FILING DATE **EXAMINER DOCUMENT** INITIALS NUMBER **NAME CLASS** SUBCLASS (IF APPRO.) DATE 5/8/2001 Doyle et al. 6,228,694 B1 6/18/2002 6,406,973 B1 Lee Doyle et al. 6,281,532 B1 8/28/2001 Candelaria 5,683,934 11/4/97 Kuhn, et al. 6,368,931 B1 4/9/2002 Konishi et al. 5,310,446 5/10/94 8/1/89 Tsaur et al. 4,853,076 7/11/2002 Doyle et al. US 2002/0090791 A1 US 2002/0074598 A1 6/20/2002 Doyle et al. 7/21/2003 Jan et al. 6,509,618 B2 Shimizu et al. 11/5/2002 6,476,462 B2 3/26/2002 6,362,082 B1 Doyle et al. 5/8/2001 Doyle et al. 6,228,694 B1 5,565,697 10/15/96 Asakawa et al. US 2003/0040158 A1 2/27/2003 Saitoh Roberds et al. US 2002/0086472 A1 7/4/2002 2/18/2003 Jan et al. 6,521,964 B1 6,506,652 01/14/03 Jan et al. FOREIGN PATENT DOCUMENTS **DOCUMENT TRANSLATION CLASS** SUBCLASS **COUNTRY NUMBER DATE** YES NO OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) DATE CONSIDERED **EXAMINER**

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		US 2003/0032261 A1	2-13-03	Yeh, et a	l.					
MM		US 2003/0040158 A1	2-27-03	Saitoh						
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M		5,134,085	7-28-92	Gilgen,	et al.					
		5,310,446	5-10-94	Konishi	i, et al.		·			
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	·	5,557,122	9-17-96	Shrivas	stava, et al.				
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		5,840,593	11-24-98	Leedy						
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Docket Number (Optional) Application Number 10/710,608 PIS920040150US1 INFORMATION DISCLOSURE CITATION Applicant(s) Cheng, et al. (Use several sheets if necessary) Group Art Unit Filing Date 2812 7/23/04 **U.S. PATENT DOCUMENTS EXAMINER** PILING DATE **CLASS** DATE **SUBCLASS** REP DOCUMENT NUMBER NAME INITIAL IF APPROPRIATE 6-12-01 6,246,095 Brady, et al. 6,255,169 Li, et al. 7-3-01 6,261,964 Wu, et al. 7-17-01 6,265,317 Chiu, et al. 7-24-01 8-14-01 Wang 6,274,444 U.S. PATENT APPLICATION PUBLICATIONS **EXAMINER** FILING DATE DATE NAME **CLASS** SUBCLASS REF DOCUMENT NUMBER INITIAL IP APPROPRIATE FOREIGN PATENT DOCUMENTS Translation SUBCLASS REF DOCUMENT NUMBER DATE COUNTRY **CLASS** YE\$ NO (Including Author, Title, Date, Pertinent Pages, Etc.) **OTHER DOCUMENTS** J.H. Van Der Merwe, "Regular Articles". Journal of Applied Physics, Volume 34, No. 1, January 1963, pp. 117-122. J.W. Matthews, et al., "Defects in Epitaxial Multilayers". Journal of Crystal Growth 27 (1974), pp. 118-125. DATE CONSIDERED **EXAMINER** EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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